

Day1: July 13th 2023	Scope	Presenter	Title
08:45 – 09:00	Opening remarks & house keeping		
09:00 – 10:30	First Session		
09:00 – 09:30	Speaker I	Peter Parbrook	MOVPE of III-N nanostructures, and challenges in extending the III-N material composition range.
09:30 – 10:00	Speaker II	Laetitia Vincent	Epitaxy of hexagonal Ge-2H: growth regimes and related I3 defects
10:00 – 10:30	Speaker III	Menno Kappers	Recent progress in cubic GaN MOVPE
10:30 – 11:15	Coffee break/poster session/exhibition		
11:15 – 12:45	Second Session		
11:15 – 11:45	Speaker IV	Michael Nolan	Surface Chemistry Driving Deposition and Etch Processes: a View from the Atomic Level
11:45 – 12:15	Speaker V	Dimitri Vvedensky	Fundamentals of MOVPE growth: Lessons from molecular-beam epitaxy
12:15 – 12:45	Speaker VI	Francesco Montalenti	Morphological evolution of films and nanostructures by state-of-the-art Machine Learning approaches
12:45 – 14:15	Lunch/poster session/exhibition		
14:15 – 15:15	Third Session		
14:15 – 14:45	Speaker VII	Christophe Durand	M-plane core-shell AlGaIn growth: from quantum wells to digital alloys
14:45 – 15:15	Speaker VIII	Blandine Alloing	Selective area growth of GaN: pendeoepitaxy on SOI and core-shell nanowires.
15:15 – 16:30	Coffee break/poster session/exhibition		
16:30 – 17:30	Fourth Session		
16:30 – 17:00	Speaker IX	Andre Strittmatter	Local epitaxial growth by laser-assisted MOVPE
17:00 – 17:30	Speaker X	Wouter Peeters	Critical length of wurtzite GaAs nanowires
19:00	Social Dinner		
Day2: July 14th 2023			
09:00 – 10:30	First Session		
09:00 – 09:30	SpeakerXI	Erik Bakkers	Epitaxy of hexagonal SiGe
09:30 – 10:00	SpeakerXII	Bernardette Kunert	III-V Nano-Ridge Engineering for device integration to Si substrate
10:00 – 10:30	Speaker XIII	Lucia Sorba	Free-standing InSb nanostructures: growth, morphology control and electrical characterization
10:30 – 11:15	Coffee break/poster session/exhibition		
11:15 – 12:45	Second Session		
11:15 – 11:45	Speaker XIV	Emanuele Pelucchi	Zinc, Oxygen and others which behave interestingly (aka strangely) in MOVPE
11:45 – 12:15	Speaker XV	Hannah J. Joyce	TBD
12:15 – 12:45	Speaker XVI	Arnab Bhattacharya	Why low-budget MOVPE is possible? Adventures in epitaxial growth in India
12:45 – 14:15	Lunch/poster session/exhibition		
14:15 – 15:15	Third Session		
14:15 – 14:45	Speaker XVII	Michael Jetter	Thin-film InGaAs metamorphic buffer for telecom C-band QDs on GaAs
14:45 – 15:15	Speaker XVIII	Elisa M Sala	Growth and characterization of InAs/InP quantum dots by droplet epitaxy in MOVPE at the telecom C-band for quantum information technologies
15:15 -15:30	Sponsor talk	Bruker	Presentation from Bruker
15:30 – 16:45	Coffee break /poster session/exhibition		
16:45 – 17:45	Fourth Session		
16:45 – 17:15	Speaker XIX	Elizaveta Semenova	Droplet mediated epitaxy
17:15 – 17:45	Speaker XX	Heinz Schmid	Selective epitaxy and metastable semiconductors
End			